IN THE CLAIMS

Claim 9 has been amended as follows:

9. (Amended) A method to form bonding pad openings that prevent tape residue in the manufacture of an integrated circuit device comprising:

providing a semiconductor substrate;

depositing a passivation layer overlying said semiconductor substrate;

depositing an organic photoresist layer overlying said passivation layer;

patterning said organic photoresist layer to expose said passivation layer in areas where passivation openings are planned;

reflowing said organic photoresist layer to create gradually sloping sidewalls on said organic photoresist layer wherein said reflowing is performed at a temperature of between 140 degrees C and 200 degrees C for a duration of between 3 minutes and 15 minutes;

etching through said passivation layer not covered by said organic photoresist layer to form said passivation openings with gradually sloping sidewalls;

stripping away said organic photoresist layer;

applying a protective tape overlying said passivation layer and said passivation openings; and

removing said protective tape wherein said gradually sloping sidewalls on said passivation openings allow the protective tape to be completely removed without leaving adhesive residue.

Claim 13 has been amended as follows:

13. (Amended) The method according to Claim 9 wherein said step of removing said protective tape is by use of a peeling tape.

Claim 16 has been amended as follows:

16. (Amended) A method to form bonding pad openings that prevent tape residue in the manufacture of an integrated circuit device comprising:

providing a semiconductor substrate;

providing a metal layer overlying said semiconductor substrate;

depositing a passivation layer overlying said metal layer;

depositing an organic photoresist layer overlying said passivation layer;

patterning said organic photoresist layer to expose said passivation layer in areas overlying said metal layer where said bonding pad openings are planned;

reflowing said organic photoresist layer to create gradually sloping sidewalls on said organic photoresist layer wherein said reflowing is performed at a temperature of between 140 degrees C and 200 degrees C for a duration of between 3 minutes and 15 minutes;

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etching through said passivation layer not covered by said passivation layer to form said bond pad openings with gradually sloping sidewalls;

stripping away said organic photoresist layer;

applying a protective tape overlying said passivation layer and said bond pad openings; and

removing said protective tape wherein said gradually sloping sidewalls on said passivation openings allow the protective tape to be completely removed without leaving adhesive residue and wherein said removing is by use of a peeling tape in the manufacture of the integrated circuit device.

Claim 19 has been amended as follows: